

Customer Technical Update With LAYTEC



Thursday 12th December 2024 commencing 13:30

TIME	ТОРІС	PRESENTER
10 min	 Welcome, Introduction Company Overview Corporate Organization and Oxford Instruments Plasma Technology. Workshop objective. 	Gohda-san - Oxford Instruments
30 min	 InP and GaAs lasers – III-V Material Processing Production solution for etching of InP transceivers and GaAs VCSEL. Etch III-V etching process overview for R&D. 	Dr Ligang Deng - Oxford Instruments
30 min	 SiC PE - Material Processing Plasma etch and deposition solutions for current and next generation SiC power devices. SiC substrate Epi ready cost reduction for 150mm and 200mm wafers with plasma polishing. 	lan Wright - Oxford Instruments
15 min	Coffee Break sponsored by Hakuto	
30 min	 GaN PE/RF - Atomic Scale Processing Production-qualified Plasma Atomic Layer Deposition for GaN HEMT passivation. Low damage, reliable etch processes for p-GaN HEMT and recessed MISHEMT manufacturing. 	Dr Aileen O'Mahony - Oxford Instruments
20 min	Endpoint solutionsLeading endpoint accuracy.End pointing materials.	Dr Yuto Tomita - Laytec
10 min	Wrap up and next steps • Q&A • Further engagement.	Robert Gunn - Oxford Instruments
60 min	Happy hour	